

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK3075

RF POWER MOSFET FOR VHF-AND UHF-BAND POWER AMPLIFIER

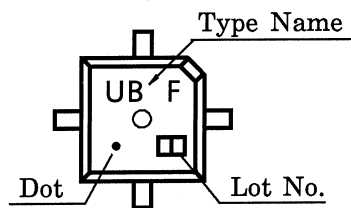
- Output Power : $P_O \geq 7.5W$
- Power Gain : $G_P \geq 11.7dB$
- Drain Efficiency : $\eta_D \geq 50\%$

MAXIMUM RATINGS (Ta = 25°C)

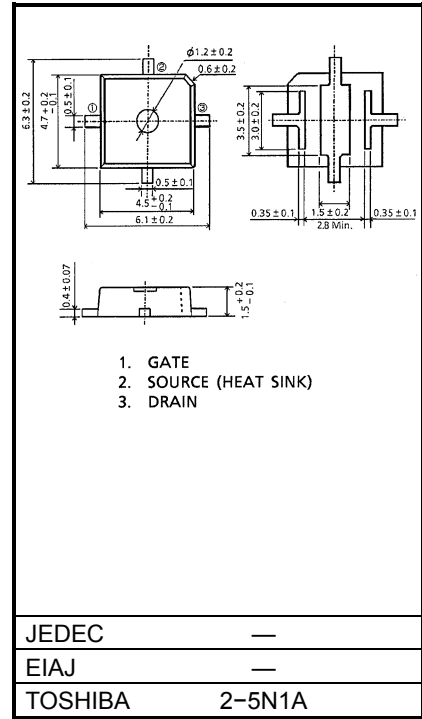
CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	25	V
Drain Current	I_D	5	A
Drain Power Dissipation	P_{D^*}	20	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-45~150	°C

*: $T_c = 25^\circ C$ When mounted on a 1.6mm glass epoxy PCB

MARKING



Unit: mm



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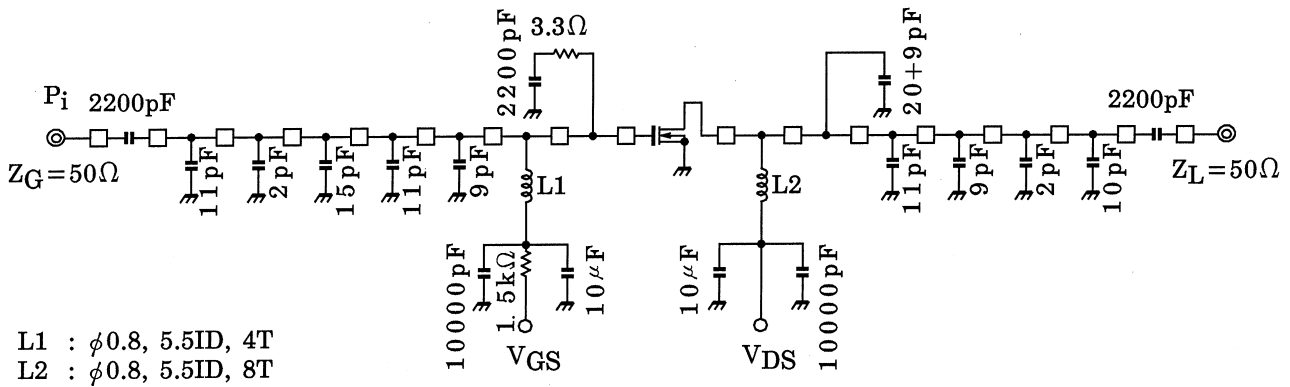
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

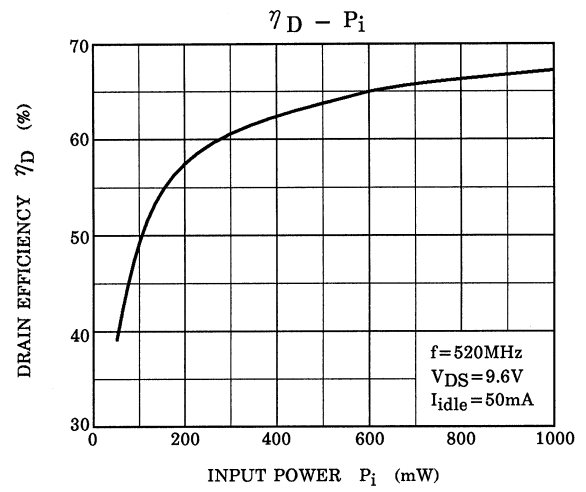
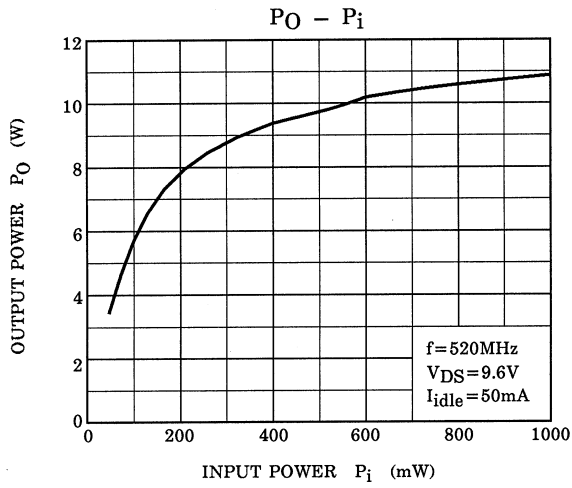
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Output Power	P_O	$V_{DS} = 9.6V$ $I_{idle} = 50mA$ ($V_{GS} = \text{adjust}$) $f = 520MHz$, $P_i = 500mW$ $Z_G = Z_L = 50\Omega$	7.5	—	—	W
Drain Efficiency	η_D		50	—	—	%
Power Gain	G_P		11.7	—	—	dB
Gate Threshold Voltage	V_{th}	$V_{DS} = 9.6V$, $I_D = 0.5mA$	1.0	1.5	2.0	V
Drain Cut-off Current	I_{DSS}	$V_{DS} = 20V$, $V_{GS} = 0$	—	—	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = 10V$, $V_{DS} = 0$	—	—	5	μA

HANDLING PRECAUTION

- When handling individual devices, be sure that working desks, human bodies and soldering iron are protected against electrostatic electricity.

RF OUTPUT POWER TEST FIXTURE





CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.